ITS30F03

Medium Frequency Powerline N-Channel IGBT

Supersedes April 1998, version DS4925-1.2

DS4925-2.2 February 1999

The ITS30F03 is a robust n-channel, enhancement mode insulated gate bipolar transistor (IGBT) designed for low power dissipation in a wide range of low to medium voltage applications such as power supplies, lighting ballasts and motor drives. The high impedance gate simplifies gate drive considerations, allowing operation directly from low power control circuitry.

Fast rise and fall times allow high frequency operation making the device suitable for the latest systems employing high frequency switching.

Low saturation voltages minimise power dissipation, thereby reducing the running cost of the overall system in which they are used.

The ITS is fully short circuit rated making it especially suited for motor control and other arduous applications.

Typical applications include high frequency inverters for motor control, automotive, welding and heating apparatus. The Powerline range of IGBTs is also applicable to switched mode and uninterruptible power supplies.

Features

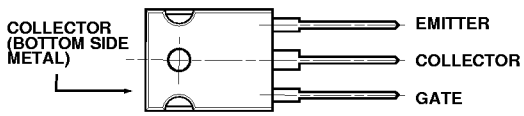
- Enhancement Mode n-Channel Device
- High Switching Speed
- Low On-state Saturation Voltage
- High Input Impedance Simplifies Gate Drive
- Latch-Free Operation
- Short Circuit Rated
- Pspice Model Data Provided

Applications

- High Frequency Inverters
- Motor Control
- Switched Mode Power Supplies
- High Frequency Welding
- Battery Truck Drives
- Automotive

Key Parameters

V_{CES}	(max)	300V
$V_{CE(sat)}$	(typ)	1.8V
I_{C25}	(max)	54A
I_{C100}	(max)	30A
I_{CM}	(max)	60A
t_{sc}	(max)	10µs



Outline type code: TO247

(See Package Details for further information)

Fig.1 Pin connections - top view (not to scale)

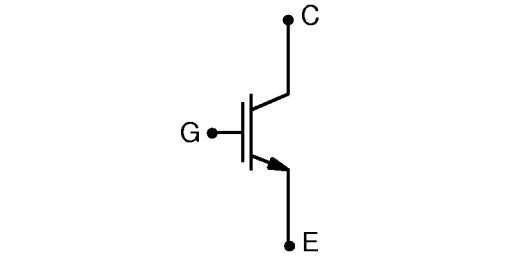


Fig.2 ITS30F03 circuit

Ordering Information

Order as:

ITS30F03P TO247 package

Note: When ordering use complete part number.

Caution: These devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

Absolute Maximum Ratings

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to Absolute Maximum Ratings for extended periods may affect device reliability.

T_{case} = 25˚C unless stated otherwise.

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	V_{GE} = 0V	300	V
V_{GES}	Gate-emitter voltage	-	±20	V
I_{C25}	Continuous collector current	T_{case} = 25˚C	54	A
I_{C85}	Continuous collector current	T_{case} = 100˚C	30	A
I_{CM}	Pulsed collector current	1ms, T_{case} = 100˚C	60	A
P_{tot}	Power dissipation	T_{case} = 100˚C	63	W

Thermal And Mechanical Ratings

Symbol	Parameter	Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance	DC junction to case	-	0.8	˚C/W
T_j	Operating junction temperature range	-	–40	150	˚C
T_{stg}	Storage temperature range	-	–40	150	˚C
-	Mounting torque	M3 Screw	-	1.1	Nm

DC Electrical Characteristics

T_{case} = 25˚C unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_{CES}	Collector cut-off current	V_{GE} = 0V, V_{CE} = 300V	-	-	0.5	mA
I_{GES}	Gate leakage current	V_{GE} = 20V, V_{CE} = 0V	-	-	±500	nA
$V_{GE(TH)}$	Gate threshold voltage	I_C = 1mA, V_{CE} = V_{GE}	4.0	6.0	7.5	V
$V_{CE(SAT)}$	Collector-emitter saturation voltage	V_{GE} = 15V, I_C = 30A	-	1.8	2.4	V
		V_{GE} = 15V, I_C = 30A T_j = 125˚C	-	1.9	-	V

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AC Electrical Characteristics

T_{case} = 25˚C unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
C_{ies}	Input capacitance	V_{CE} = 25V, V_{GE} = 15V, f = 1MHz	-	2000	-	pF
C_{oes}	Output capacitance	V_{CE} = 25V, V_{GE} = 15V, f = 1MHz	-	520	-	pF
C_{res}	Reverse transfer capacitance	V_{CE} = 25V, V_{GE} = 15V, f = 1MHz	-	450	-	pF

Inductive Switching Characteristics

T_{case} = 25˚C unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$t_{d(ON)}$	Turn-on delay time	I_C = 30A V_{GE} = ±15V, V_{CE} = 50%V_{ces} $R_{G(ON)}$ = $R_{G(OFF)}$ = 25Ω	-	330	-	ns
t_r	Rise time		-	90	-	ns
E_{ON}	Turn-on energy loss - per cycle		-	300	-	µJ
$t_{d(OFF)}$	Turn-off delay time		-	260	-	ns
t_f	Fall time		-	270	350	ns
E_{OFF}	Turn-off energy loss - per cycle		-	1000	-	µJ

T_{case} = 125˚C unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$t_{d(ON)}$	Turn-on delay time	I_C = 30A V_{GE} = ±15V, V_{CE} = 50%V_{ces} $R_{G(ON)}$ = $R_{G(OFF)}$ = 25Ω	-	330	-	ns
t_r	Rise time		-	90	-	ns
E_{ON}	Turn-on energy loss - per cycle		-	330	-	µJ
$t_{d(OFF)}$	Turn-off delay time		-	280	-	ns
t_f	Fall time		-	370	-	ns
E_{OFF}	Turn-off energy loss - per cycle		-	1300	-	µJ

Short Circuit Rating

T_{case} = 125˚C unless stated otherwise.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
t_{sc}	Short circuit withstand time	V_{GE} = 15V, V_{CE} = 50% V_{CES}	-	-	10	µs

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Pspice Model Parameters

AGD	AREA	BVF	BVN	CGS	COXD	JSNE	KF	KP
1.08E–05	1.62E–06	1	4	1.70E–07	5.00E–09	6.50E-13	1.091	2.288
MUN	**MUP**	**NB**	**TAU**	**THETA**	**VT**	**VTD**	**WB**	
1.50E+03	450	2.00E+14	1.60E–07	2.00E–02	6.402	–5	3.00E–05	

Basic Test Circuit

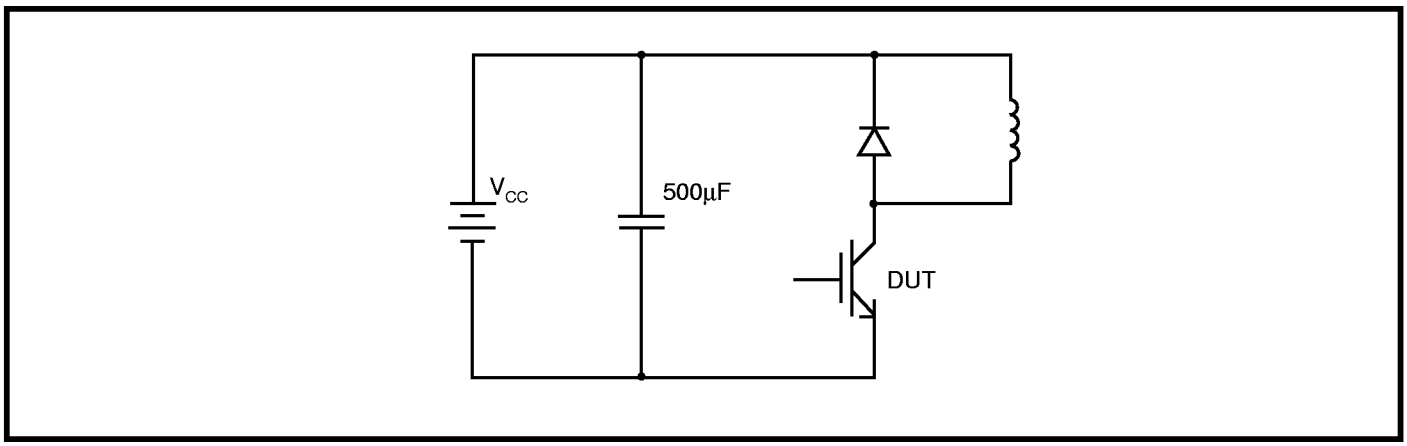

Fig.3 Basic d.c. chopper circuit

Switching Definitions

$t_r = t_3 - t_2$

$t_{d(on)} = t_2 - t_1$

$E_{on} = \int_{t_1}^{t_3 + 1\mu s} V_{CE} . I_C \, dt$

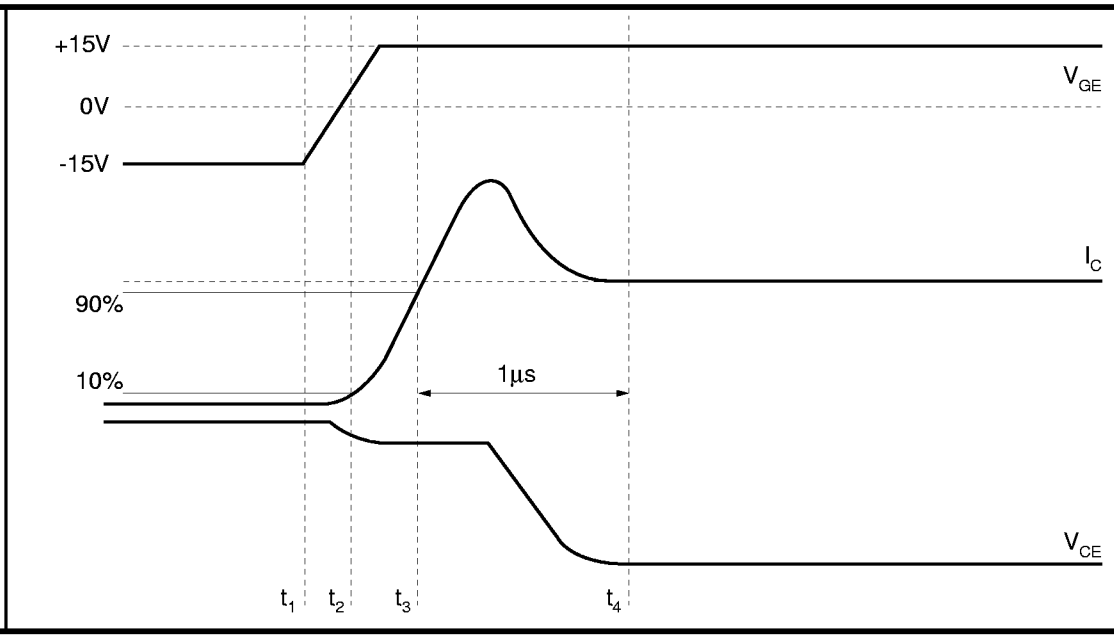

Fig.4 Turn-on characteristics

$t_f = t_7 - t_6$

$t_{d(off)} = t_6 - t_5$

$E_{off} = \int_{t_5}^{t_7 + 1\mu s} V_{CE} . I_C \, dt$

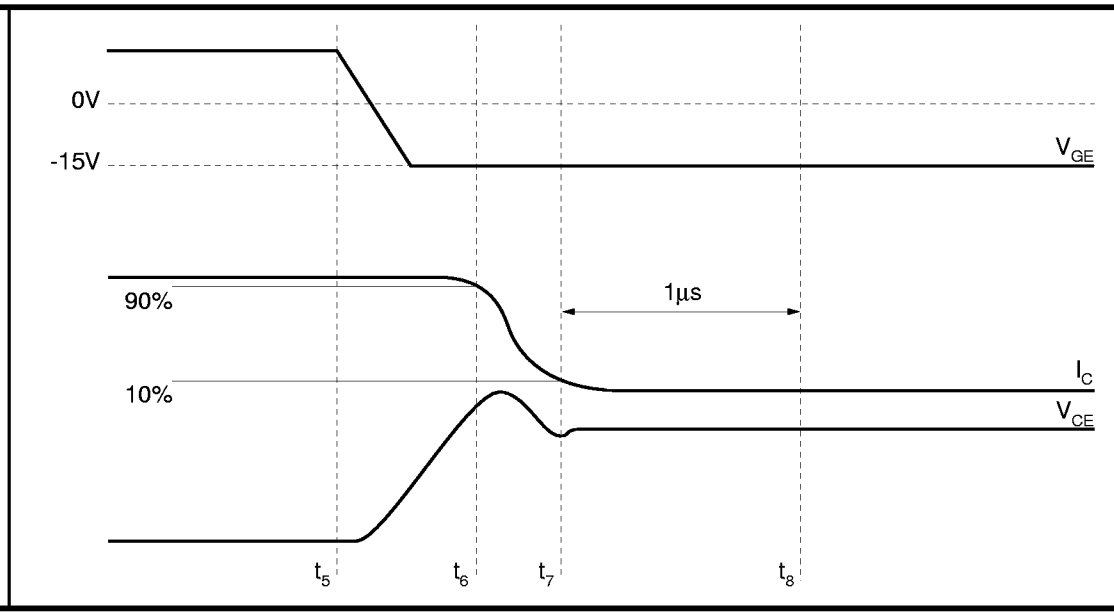

Fig.5 Turn-off characteristics

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Curves

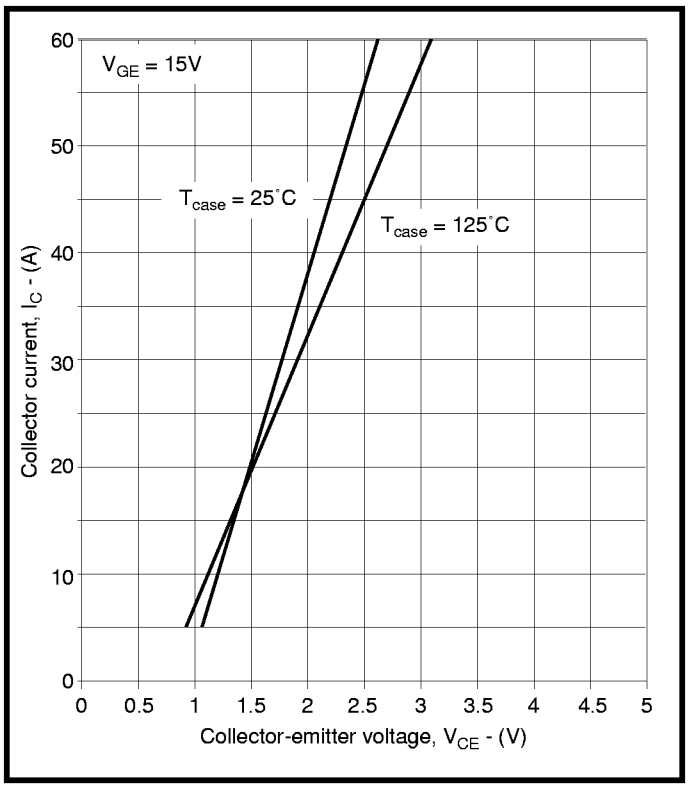

Fig.6 Typical output characteristics

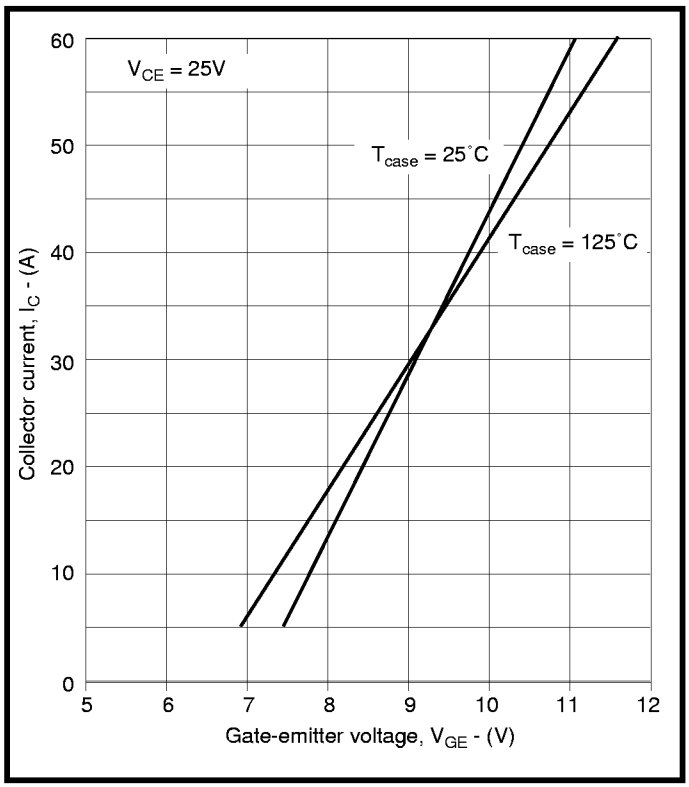

Fig.7 Typical transfer characteristics

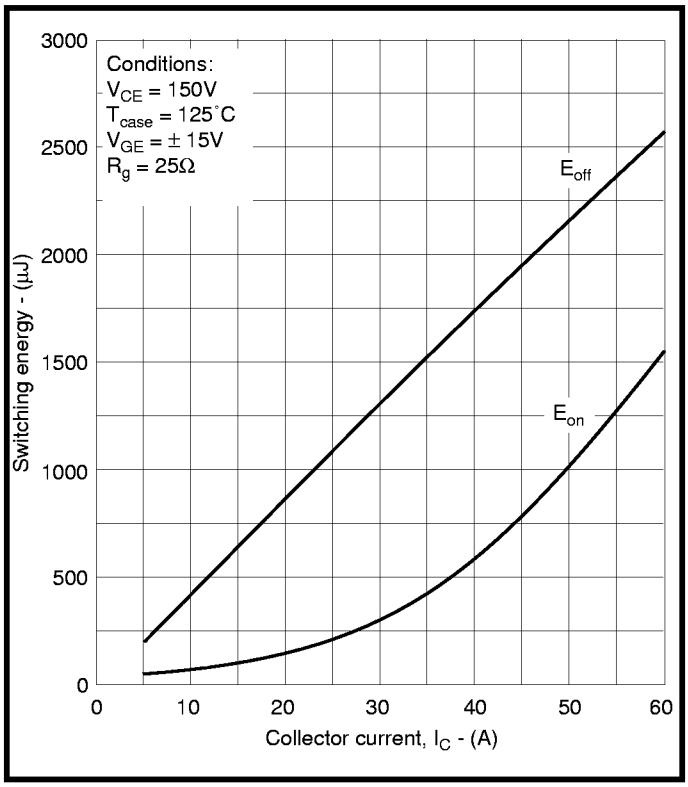

Fig.8 Typical switching losses vs collector current

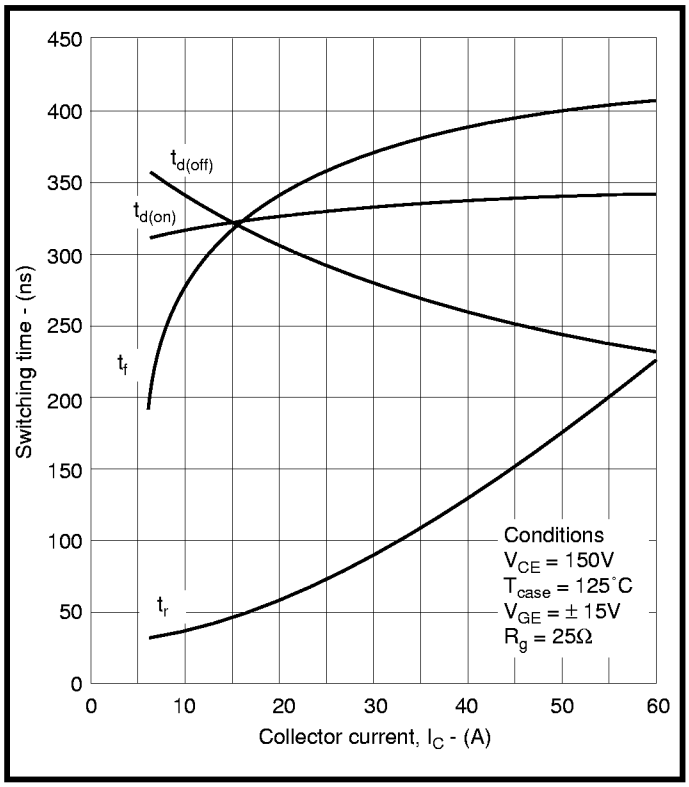

Fig.9 Typical switching times vs collector current

Caution: These devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

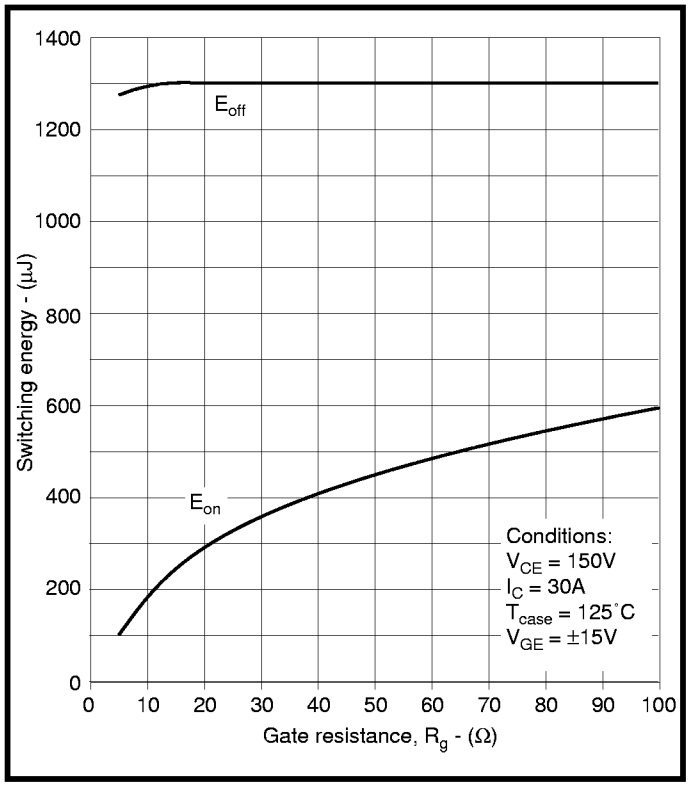

Fig.10 Typical switching losses vs gate resistance

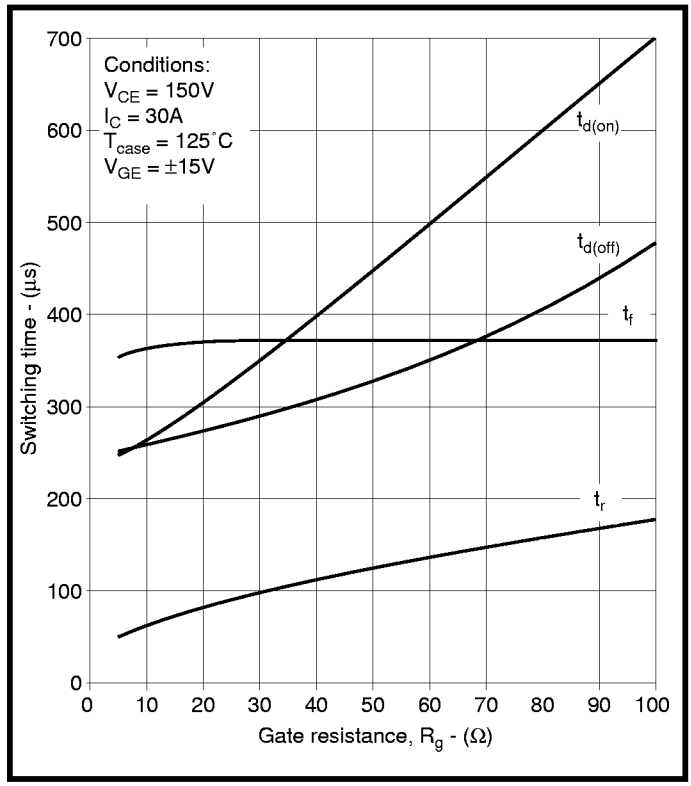

Fig.11 Typical switching times vs gate resistance

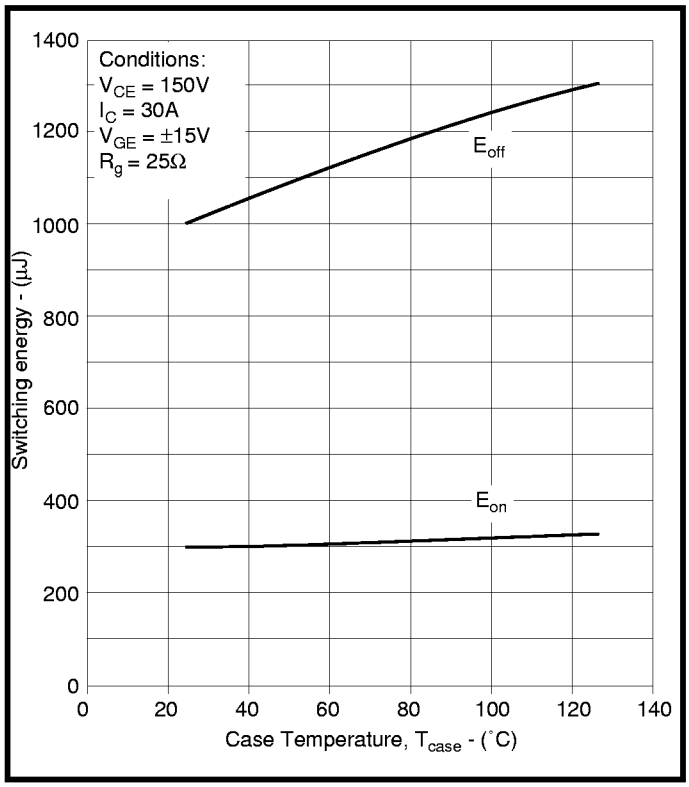

Fig.12 Typical switching losses vs case temperature

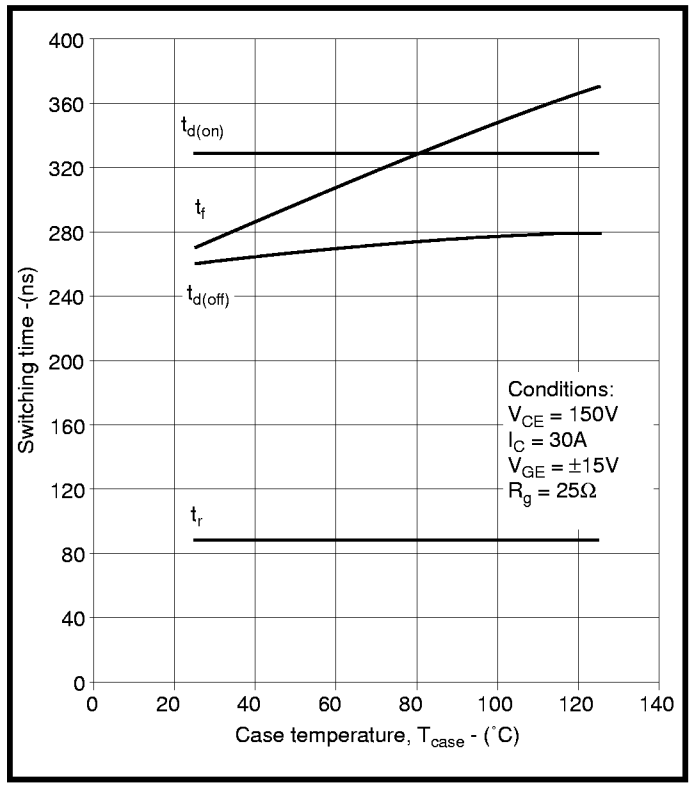

Fig.13 Typical switching times vs case temperature

Caution: These devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

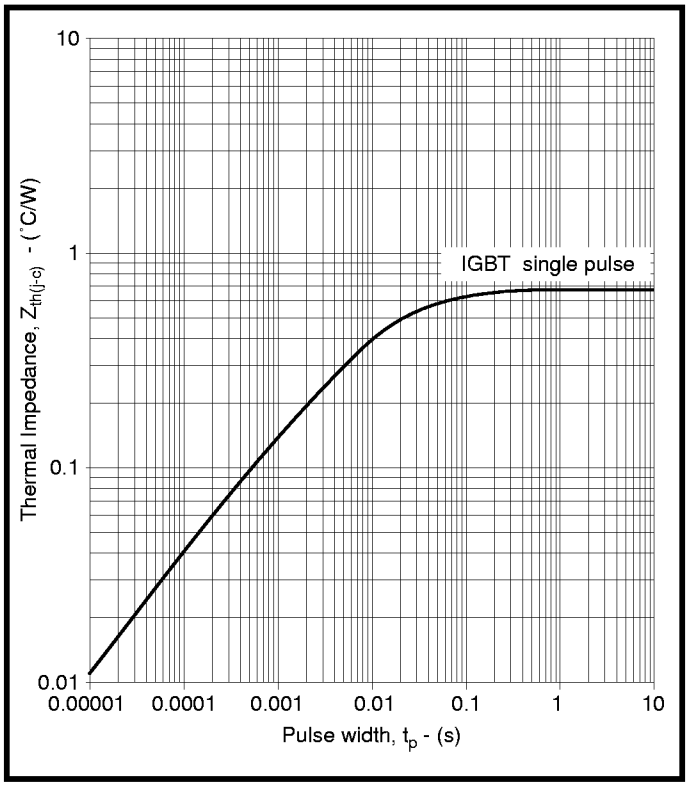

Fig.14 Transient thermal impedance - junction to case

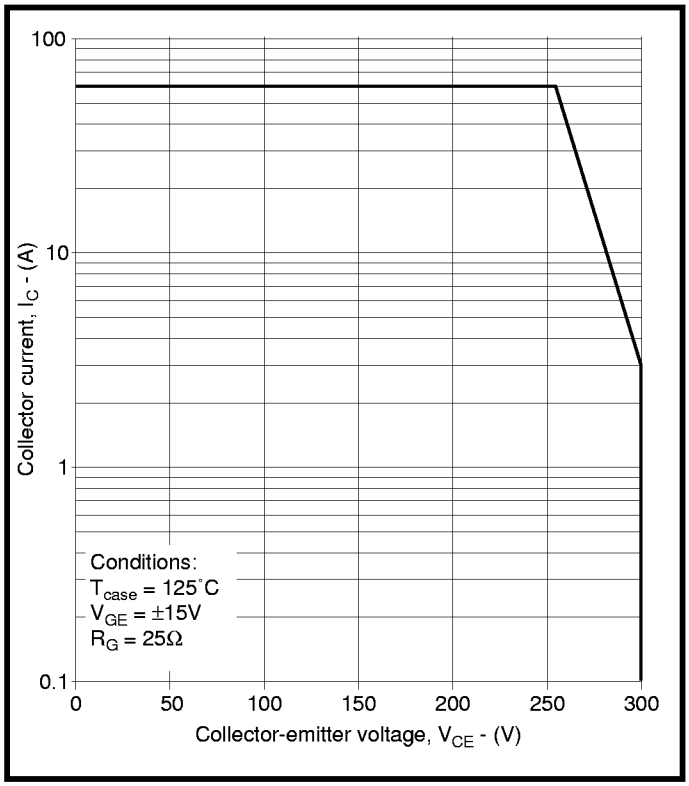

Fig.15 Reverse bias safe operating area

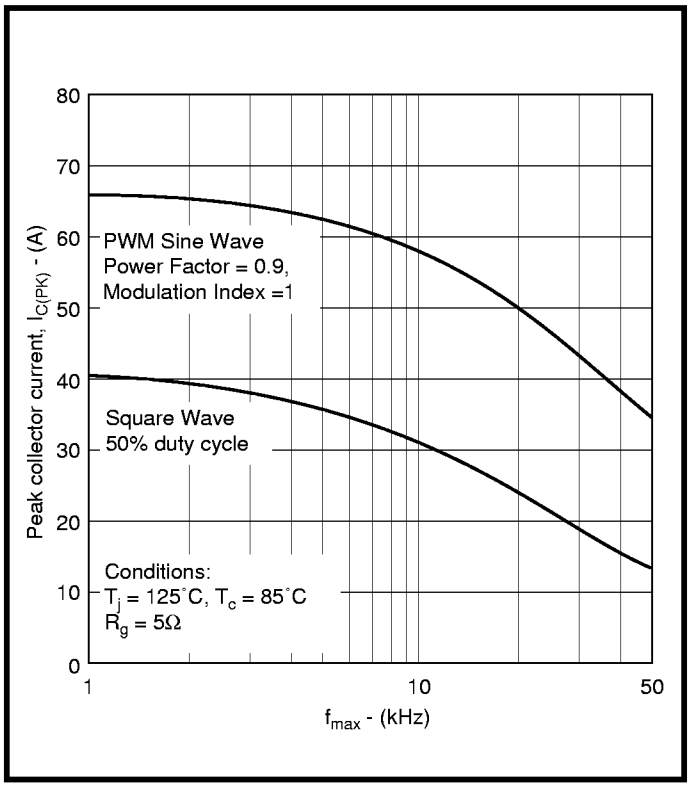

Fig.16 Three phase PWM inverter operating frequency

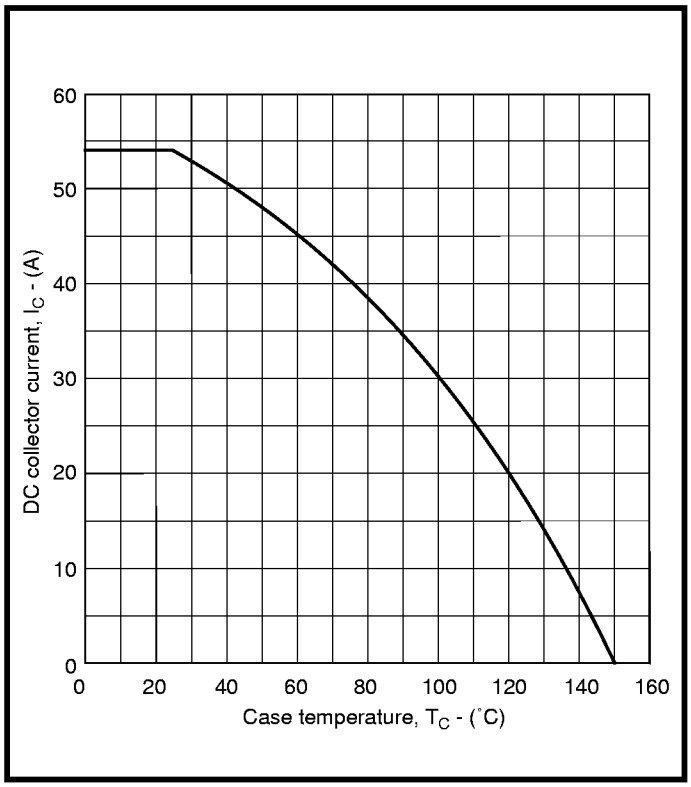

Fig.17 Collector current vs case temperature

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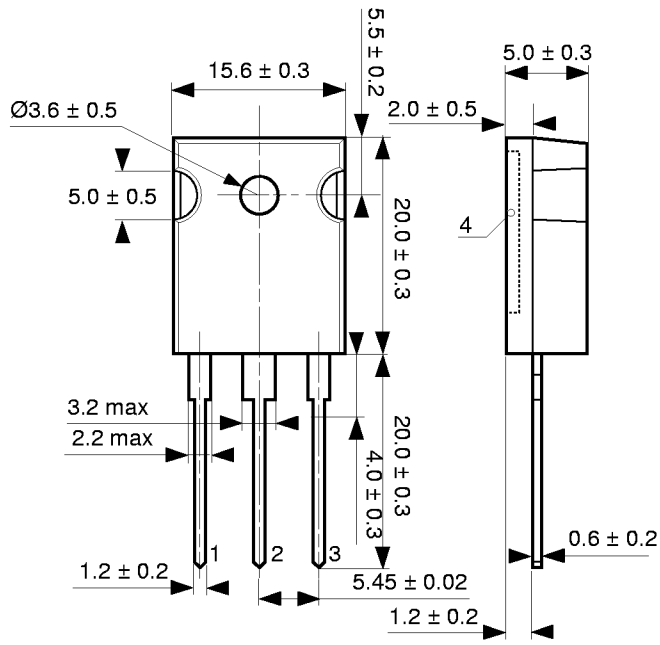
Package Details

For additional package information, please contact your nearest representative or Mitel Semiconductor Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Terminal 1 - Gate
Terminal 2 - Collector
Terminal 3 - Emitter
Terminal 4 - Collector

Package OutlineType: TO247

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